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	/ " ď	Application Number	10/706,641
INFORMATION DISCLOSURE	JUN 0 1 2006	Filing Date	11-12-2003
STATEMENT BY APPLICANT	2005	First Named Inventor	Allen
	\2, .6	Group Art Unit	2826
(use as many sheets as necessary)	PETE TRADEMARY	Examiner Name	Unknown
Sheet 1 Of	1	Attorney Docket Number	5308-127DV

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STATEMENT BY APPLICANT	8.	First Named Inventor	Scott T. Allen
	(3) AS	Group Art Unit	2826
(use as many sheets as necessary)	FIRM & TRADEMENT	Examiner Name	Ahmed N. Sefer
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